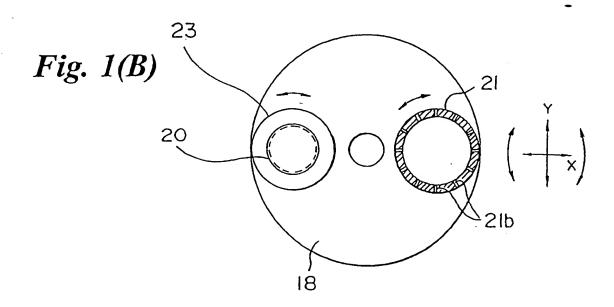
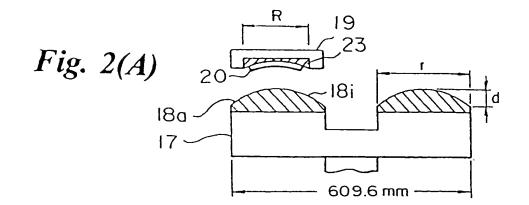


Feb. 25, 1997

17

Sheet 1 of 12



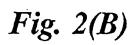




Feb. 25, 1997

Sheet 2 of 12

4. T. 4.96



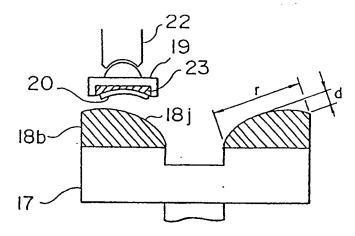


Fig. 2(C) 23

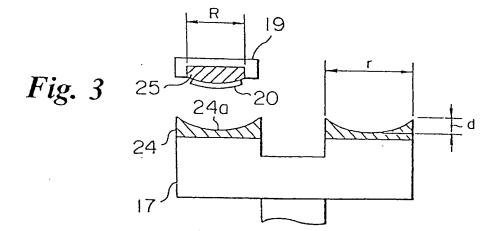
Wafer 6 inch ϕ , (r = 280 mm, Flatness 4 μ Incase of d = 4 + 8 μ)

Fig. 2(D)



Fig. 2(E)







Feb. 25, 1997

Sheet 3 of 12



Fig. 4(A)

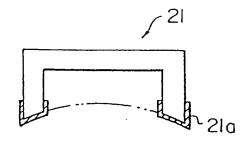


Fig. 4(B)

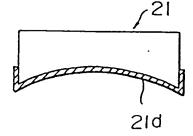
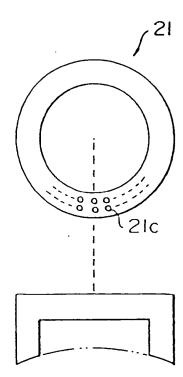


Fig. 4(C)



U.S. Patent

Feb. 25, 1997

Sheet 4 of 12

Fig. 5

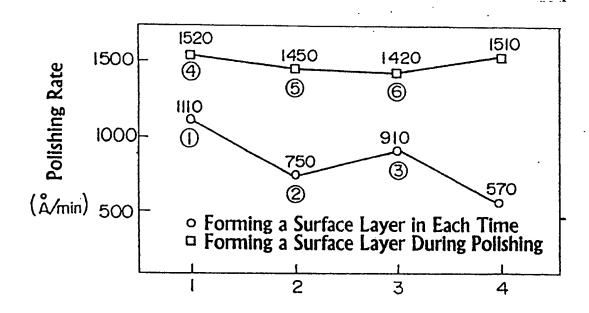
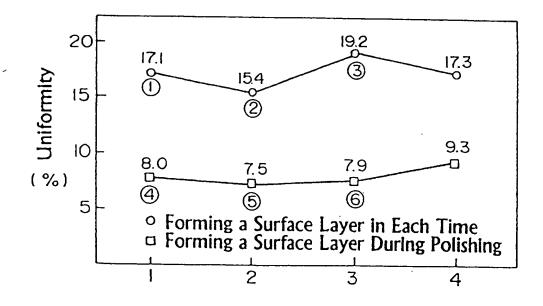


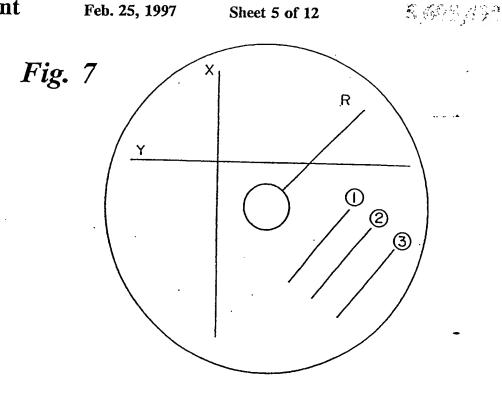
Fig. 6

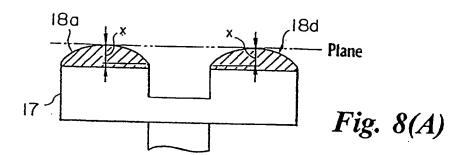


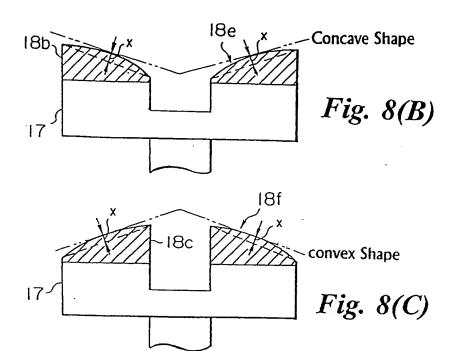
U.S. Patent

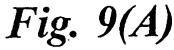
Feb. 25, 1997

Sheet 5 of 12









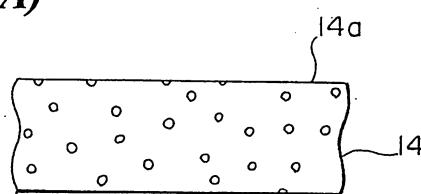
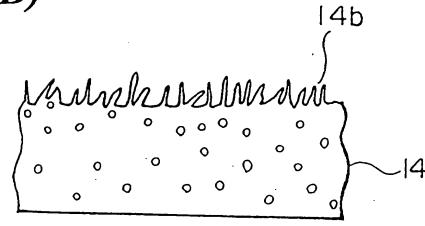


Fig. 9(B)



DESELTE TESP

Sec.

U.S. Patent

Feb. 25, 1997

Sheet 7 of 12

5,605,499

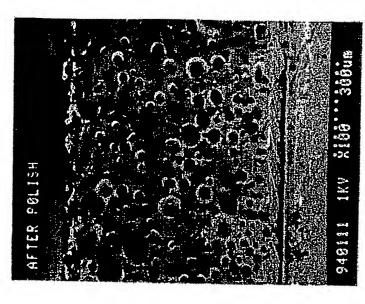


FIG 10

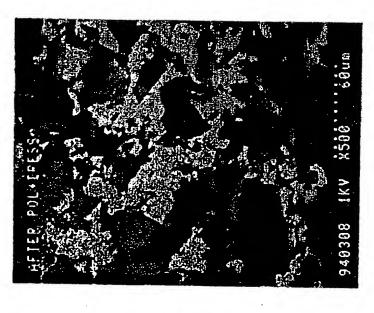


FIG. 1

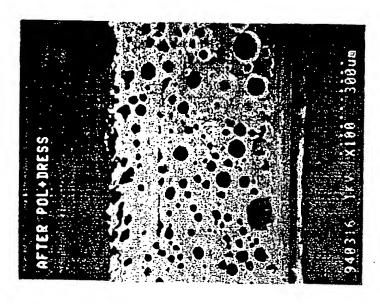
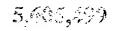


FIG. 10

U.S. Patent

Feb. 25, 1997

Sheet 8 of 12



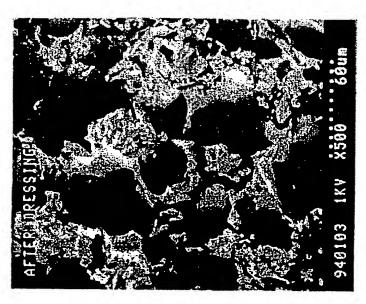


FIG.15

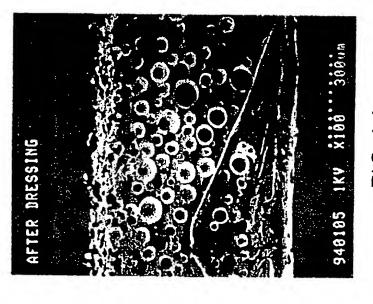
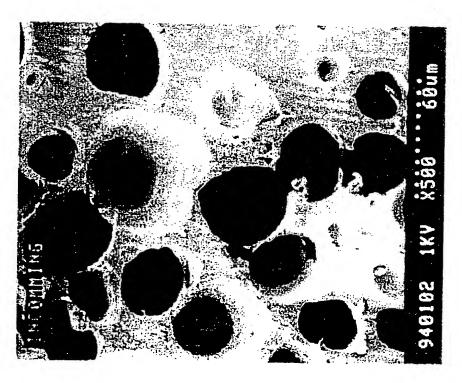


FIG.14



FIG. 13



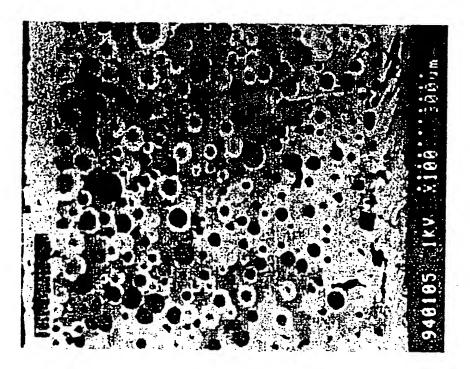


FIG. 16

To be



Sheet 10 of 12

Fig. 18

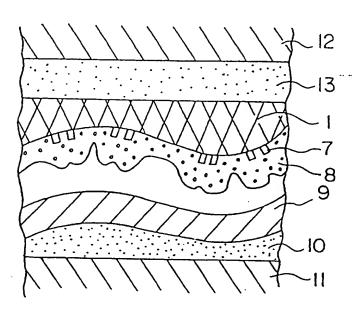


Fig. 19

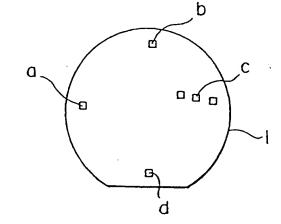
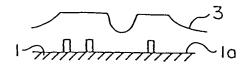
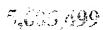


Fig. 20(A)

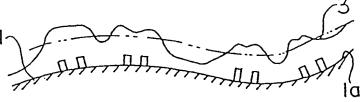
Straight Polishing



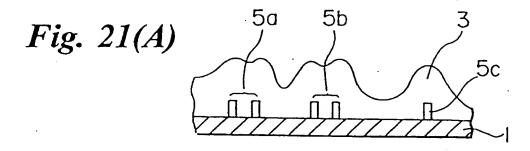
CECUL TEHDAGE







Polishing According to Unevenness of Wafer la



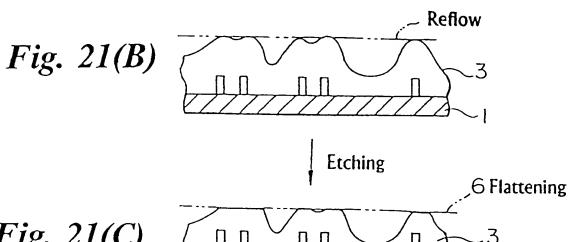
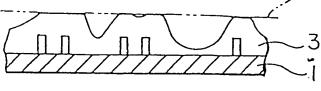


Fig. 21(C)



OSSCHEL ACSST

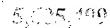
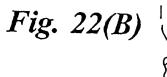


Fig. 22(A)





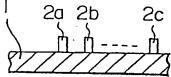


Fig. 22(C)

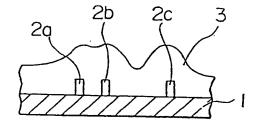


Fig. 22(D) 20_

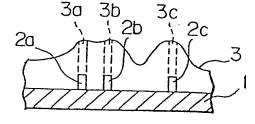


Fig. 22(E)

